BD435, BD437, BD439, BD441

Plastic Medium Power Silicon NPN Transistor

This series of plastic, medium–power silicon NPN transistors can be used for amplifier and switching applications. Complementary types are BD438 and BD442.

Features

• Pb-Free Package is Available*

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Collector–Emitter Voltage	BD435 BD437 BD439 BD441	V _{CEO}	32 45 60 80	Vdc
Collector-Base Voltage	BD435 BD437 BD439 BD441	V _{CBO}	32 45 60 80	Vdc
Emitter-Base Voltage		V _{EBO}	5.0	Vdc
Collector Current		I _C	4.0	Adc
Base Current		I _B	1.0	Adc
Total Device Dissipation @ T _C = 2 Derate above 25°C	5°C	P _D	36 288	Watts W/°C
Operating and Storage Junction Te Range	emperature	T _J , T _{stg}	-55 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	θ JC	3.5	°C/W

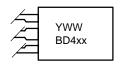


http://onsemi.com

4.0 AMPERES POWER TRANSISTORS NPN SILICON



MARKING DIAGRAM



xx = 35, 37, 39, 41 Y = Year WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping [†]
BD435	TO-225AA	500 Units/Box
BD437	TO-225AA	500 Units/Box
BD437G	TO-225AA (Pb-Free)	500 Units/Box
BD437T	TO-225AA	500 Units/Rail
BD439	TO-225AA	500 Units/Box
BD441	TO-225AA	500 Units/Box

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
Collector–Emitter Breakdown Voltage $(I_C = 100 \text{ mA}, I_B = 0)$	BD435 BD437 BD439 BD441	V _{(BR)CEO}	32 45 60 80	- - - -	- - - -	Vdc
Collector–Base Breakdown Voltage ($I_C = 100 \mu A, I_B = 0$)	BD435 BD437 BD439 BD441	V _{(BR)CBO}	32 45 60 80	- - - -	- - -	Vdc
Emitter–Base Breakdown Voltage $(I_E = 100 \mu A, I_C = 0)$		V _{(BR)EBO}	5.0	_	-	Vdc
Collector Cutoff Current $(V_{CB} = 32 \text{ V}, I_{E} = 0)$ $(V_{CB} = 45 \text{ V}, I_{E} = 0)$ $(V_{CB} = 60 \text{ V}, I_{E} = 0)$ $(V_{CB} = 80 \text{ V}, I_{E} = 0)$	BD435 BD437 BD439 BD441	I _{CBO}	- - - -	- - - -	0.1 0.1 0.1 0.1	mAdc
Emitter Cutoff Current (V _{EB} = 5.0 V)		I _{EBO}	_	_	1.0	mAdc
DC Current Gain (I _C = 10 mA, V _{CE} = 5.0 V)	BD435 BD437 BD439 BD441	h _{FE}	40 30 20 15	- - - -	- - - -	
DC Current Gain ($I_C = 500 \text{ mA}, V_{CE} = 1.0 \text{ V}$)	BD435 BD437 BD439, BD441	h _{FE}	85 85 40	- - -	475 375 475	
DC Current Gain (I _C = 2.0 A, V _{CE} = 1.0 V)	BD435 BD437 BD439 BD441	h _{FE}	50 40 25 15	- - - -	- - - -	
Collector Saturation Voltage ($I_C = 2.0 \text{ A}, I_B = 0.2 \text{ V}$) ($I_C = 3.0 \text{ A}, I_B = 0.3 \text{ A}$)	BD435 BD437, BD439, BD441	V _{CE(sat)}	_ _	_ _	0.5 0.8	Vdc
Base-Emitter On Voltage (I _C = 2.0 A, V _{CE} = 1.0 V)		V _{BE(on)}	_	_	1.1	Vdc
Current–Gain – Bandwidth Product $(V_{CE} = 1.0 \text{ V}, I_{C} = 250 \text{ mA}, f = 1.0 \text{ MHz})$		f _T	3.0	_	-	MHz

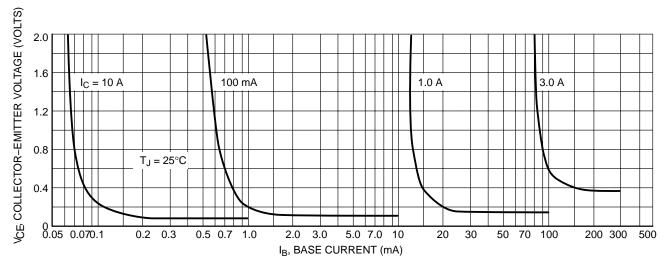


Figure 1. Collector Saturation Region

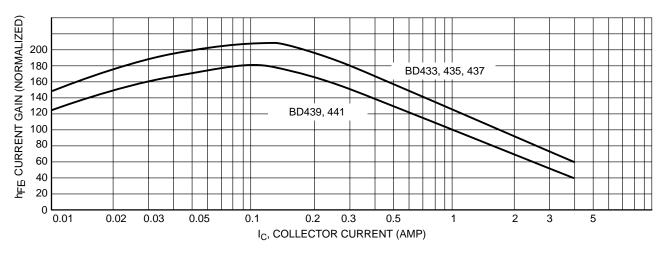


Figure 2. Current Gain

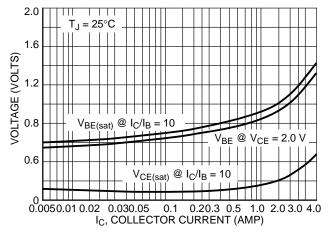


Figure 3. "On" Voltage

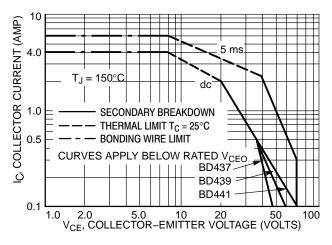
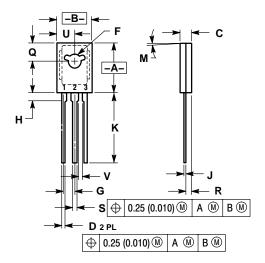


Figure 4. Active Region Safe Operating Area

BD435, BD437, BD439, BD441

PACKAGE DIMENSIONS

TO-225AA CASE 77-09 ISSUE Z



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
- 3. 077-01 THRU -08 OBSOLETE, NEW STANDARD

	INCHES		MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.425	0.435	10.80	11.04	
В	0.295	0.305	7.50	7.74	
С	0.095	0.105	2.42	2.66	
D	0.020	0.026	0.51	0.66	
F	0.115	0.130	2.93	3.30	
G	0.094 BSC		2.39 BSC		
Н	0.050	0.095	1.27	2.41	
J	0.015	0.025	0.39	0.63	
K	0.575	0.655	14.61	16.63	
M	5° TYP		5° TYP		
Q	0.148	0.158	3.76	4.01	
R	0.045	0.065	1.15	1.65	
S	0.025	0.035	0.64	0.88	
U	0.145	0.155	3.69	3.93	
٧	0.040		1.02		

STYLE 1:

EMITTER 2.

COLLECTOR BASE 3.

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